### NCE P-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE2303H uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , This device is suitable for use as a load switch or in PWM applications.

### **General Features**

•  $V_{DS} = -30V, I_{D} = -3.0A$ 

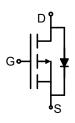
 $R_{DS(ON)}$  < 72m $\Omega$  @  $V_{GS}$ =-10V

 $R_{DS(ON)} < 118m\Omega$  @  $V_{GS}$ =-4.5V

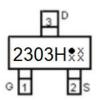
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

### **Application**

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2303H*X	NCE2303H	SOT-23	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-30	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	I <sub>D</sub>	-3.0	А	
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	-15	А	
Maximum Power Dissipation	P <sub>D</sub>	1.0	W	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C	

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	125	°C/W

### **Electrical Characteristics (T<sub>A</sub>=25℃unless otherwise noted)**

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1	μΑ



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# **NCE2303H**

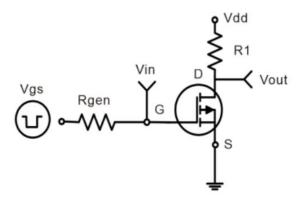
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	·			•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1	-1.6	-2.5	V
Dunin Course On Ctata Basistana		V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	-	63	72	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	-	91	118	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-3A	-	4	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ 45\/\/ O\/	-	253	-	PF
Output Capacitance	Coss	$V_{DS}$ =-15V, $V_{GS}$ =0V, F=1.0MHz	-	34	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UMHZ	-	24	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t <sub>d(on)</sub>		-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-15V,R <sub>L</sub> =5 $\Omega$	-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS}$ =-10V, $R_{GEN}$ =2 $\Omega$	-	17	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	6	-	nS
Total Gate Charge	Qg		-	8.2	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-3A,V <sub>GS</sub> =-10V	-	1.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	_	-	1.4	-	nC
Drain-Source Diode Characteristics	,		•	•		•
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-3A	-	-	-1.2	V

### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

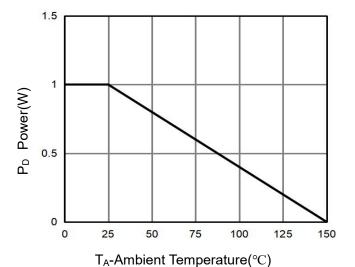
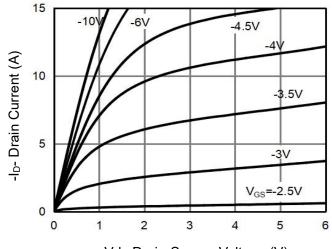


Figure 3 Power Dissipation



-Vds Drain-Source Voltage (V) **Figure 5** Output Characteristics

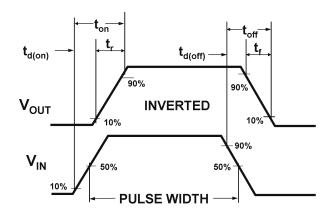


Figure 2:Switching Waveforms

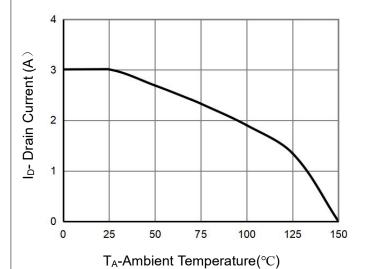


Figure 4 Drain Current

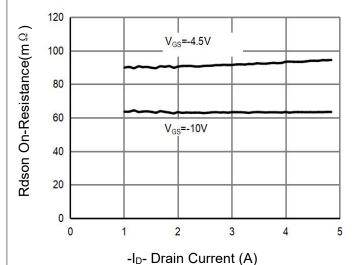
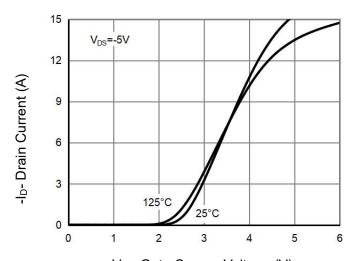


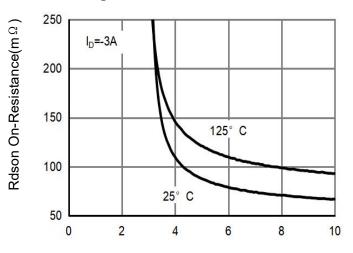
Figure 6 Drain-Source On-Resistance





-Vgs Gate-Source Voltage (V)





-Vgs Gate-Source Voltage (V)

### Figure 9 Rdson vs Vgs

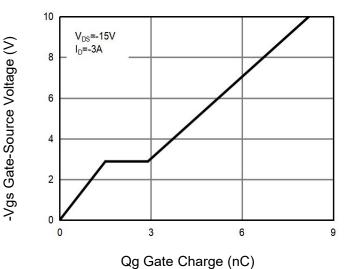
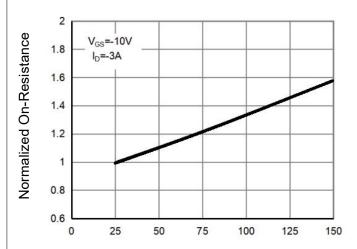


Figure 11 Gate Charge



T<sub>J</sub>-Junction Temperature(°C)

### Figure 8 Drain-Source On-Resistance

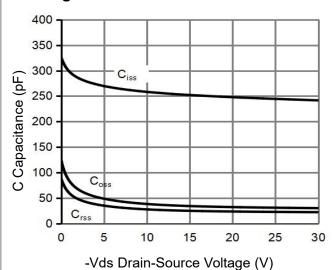
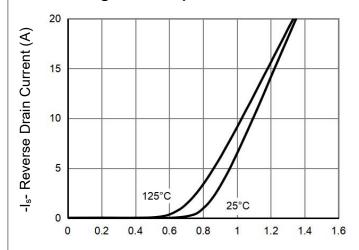


Figure 10 Capacitance vs Vds



-Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



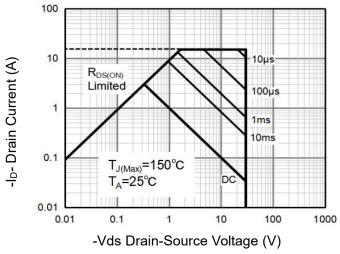
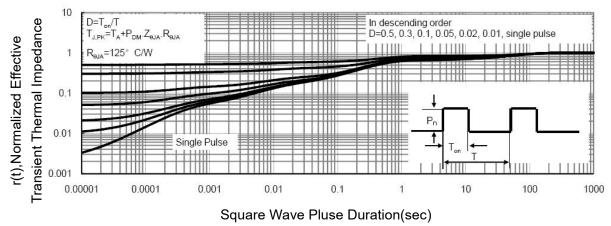


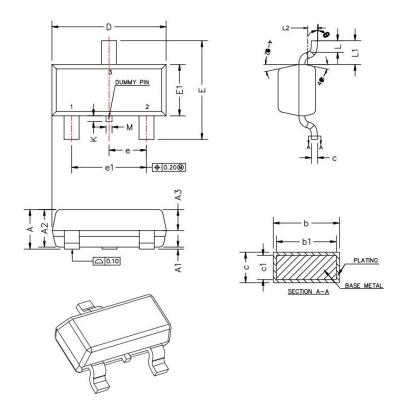
Figure 13 Safe Operation Area



**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Information**



Symbol	Millimeters			
Symbol	Min.	Max.		
Α	0.89	1.12		
A1	0.01	0.10		
A2	0.88	1.02		
A3	0.43	0.63		
b	0.36	0.50		
b1	0.35	0.45		
С	0.14	0.20		
c1	0.14	0.16		
D	2.80	3.00		
E	2.35	2.64		
E1	1.20	1.40		
е	0.90	1.00		
e1	1.80	2.00		
L	0.40	0.60		
L1	0.6REF			
L2	0.25BSC			
θ	0°	8°		
θ1	10°	14°		
θ2	10°	14°		

### **Revision History**

Revision	Date	Subjects
V1.0	2024.10.24	Product data sheet
V2.0	2025.02.24	Update R <sub>DS(ON)</sub> Max Value

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